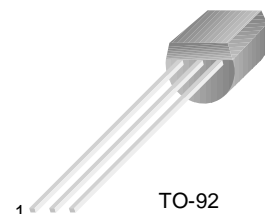


MPSA12

NPN Darlington Transistor

- This device is designed for applications requiring extremely high current gain at currents to 1.0A.
- Sourced from process 05.
- See MPSA14 for characteristics.



TO-92
1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings * $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Value | Units |
|----------------|--|------------|------------------|
| V_{CES} | Collector-Emitter Voltage | 20 | V |
| V_{CBO} | Collector-Base Voltage | 20 | V |
| V_{EBO} | Emitter-Base Voltage | 10 | V |
| I_C | Collector Current - Continuous | 1.2 | A |
| T_J, T_{STG} | Operating and Storage Junction Temperature Range | -55 ~ +150 | $^\circ\text{C}$ |

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1. These ratings are based on a maximum junction temperature of 150 degrees C.
2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Condition | Min. | Typ. | Max. | Units |
|-----------------------------|--------------------------------------|---|--------|------|------|-------|
| Off Characteristics | | | | | | |
| $V_{(BR)CES}$ | Collector-Emitter Breakdown Voltage | $I_C = 100\mu\text{A}, I_E = 0$ | 20 | | | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB} = 15\text{V}, I_E = 0$ | | | 100 | nA |
| I_{CES} | Emitter Cutoff Current | $V_{CB} = 15\text{V}, I_C = 0$ | | | 100 | nA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB} = 10\text{V}, I_C = 0$ | | | 100 | nA |
| On Characteristics * | | | | | | |
| h_{FE} | DC Current Gain | $V_{CE} = 5.0\text{V}, I_C = 10\text{mA}$ | 20,000 | | | |
| $V_{CE(sat)}$ | Collector-Emitter Saturation Voltage | $I_C = 10\text{mA}, I_B = 0.01\text{mA}$ | | | 1.0 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$ | | | 1.4 | V |

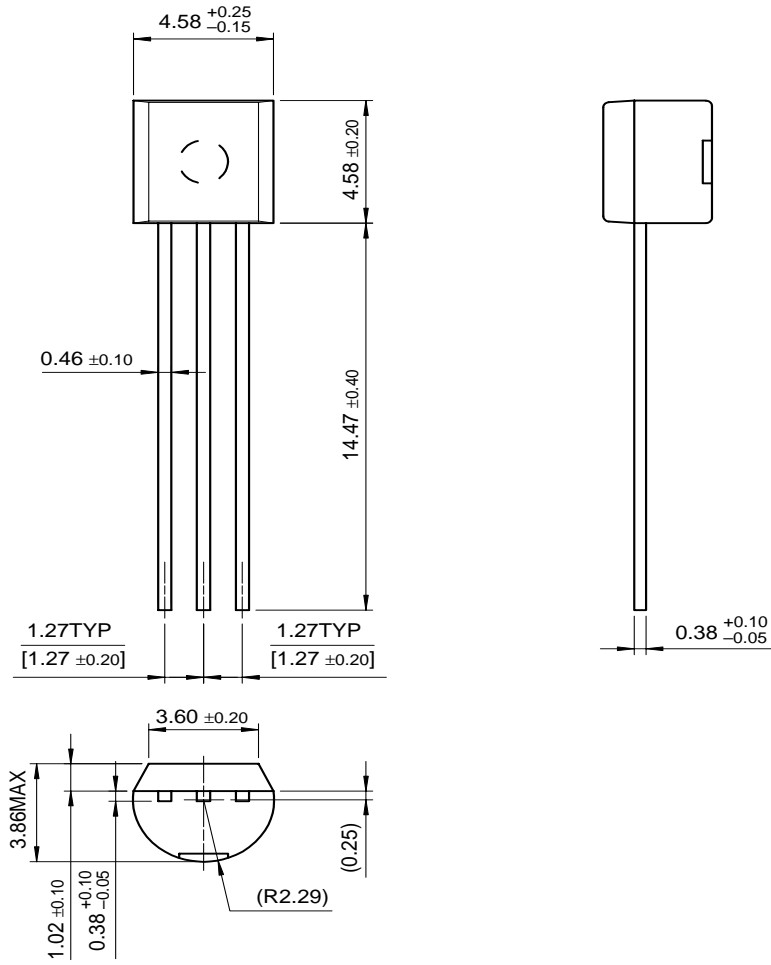
* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Thermal Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Max. | Units |
|-----------------|---|------------|----------------------------|
| P_D | Total Device Dissipation Derate above 25°C | 625 5.0 | mW mW/ $^\circ\text{C}$ |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 83.3 | $^\circ\text{C}/\text{W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 200 | $^\circ\text{C}/\text{W}$ |

Package Dimensions

TO-92



Dimensions in Millimeters

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| CROSSVOLT TM | GTO TM | POP TM | SuperSOT TM -3 | |
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